

## Red Laser Diode

### Application

Industrial use / Biomedical

### Property

Wavelength  $\lambda = 660\text{nm}$

Output Power = 100mW

Package Type =  $\phi 5.6\text{mm}$

### Introduction

Egismos currently markets AlGaInP based red laser diodes in the 635nm ~ 670nm wavelengths range. The low operating current and high temperature of the laser diodes are achieved through using misoriented substrate and MQW (Strain compensated) active layer.

Egismos laser diodes are highly rated in a broad range of applications including, but not limited to, laser pointers, green lasers, blue laser DVD, laser barcode scanners, diode laser equipments, medical instruments and aerospace applications.



### Red Laser Diode Key features

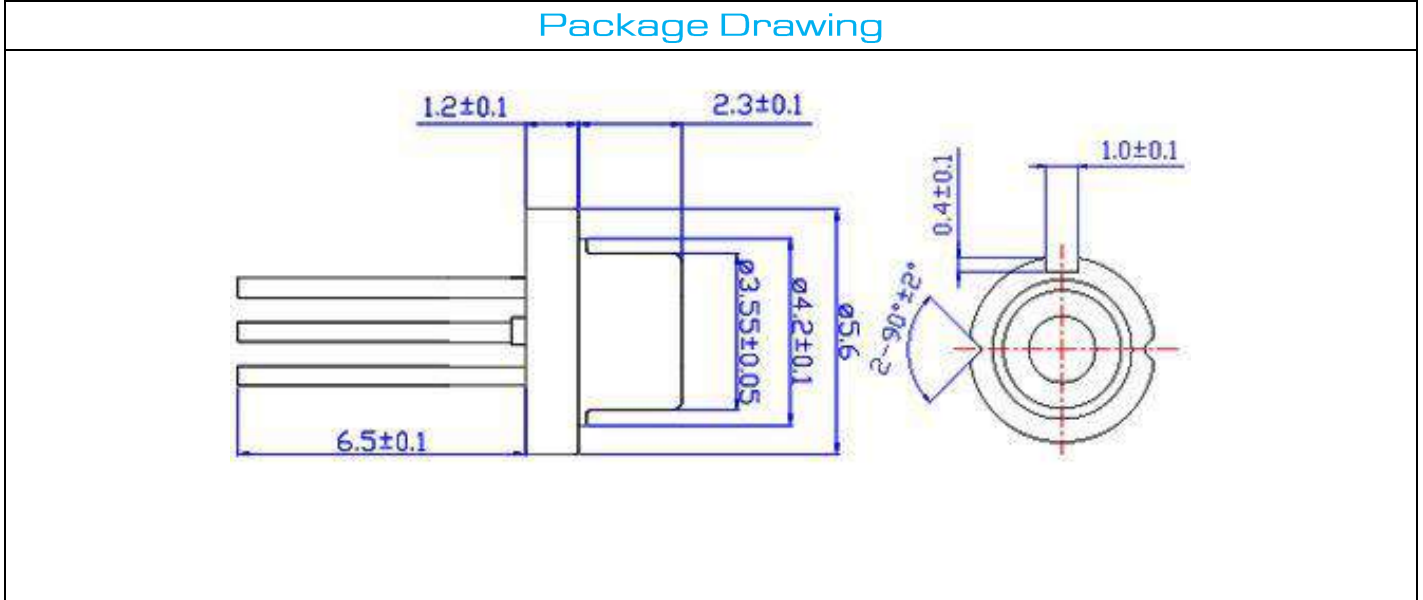
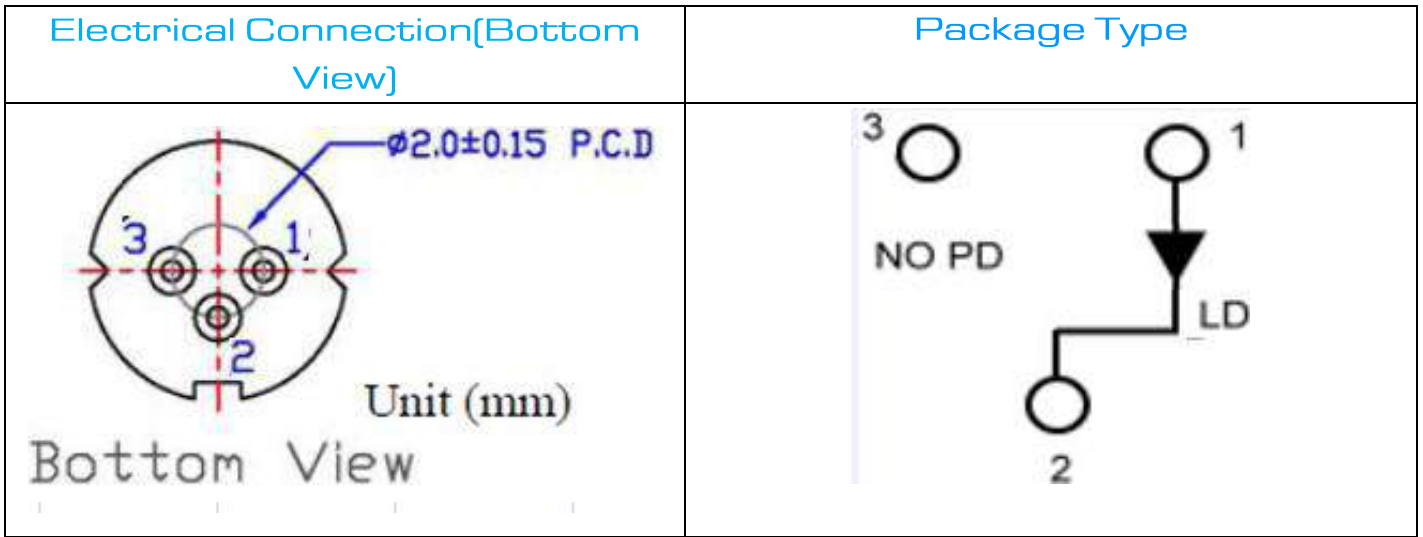
#### Absolute Maximum Rating at Tc=25°C

Items	Symbols	Values	Unit
Optical Output Power	Po(CW)	100	mW
Reverse Voltage	V	2	V
Operating Temperature	To	-10~+70	°C
Storage Temperature	Ts	-10~+70	°C

#### Electrical and Optical Characteristics at Tc=25°C

Item	Symbols	Min	Typ.	Max.	Unit	Condition
Optical Output Power	Po	-	-	100	mW	-
Threshold Current	Ith	-	55	70	mA	-
Operating Current	Iop	-	155	180	mA	Po=100mW
Operating Voltage	Vop	-	2.5	3	V	Po=100mW
Peak Wavelength	$\lambda_p$	650	660	670	nm	Po=100mW

Beam Divergence	$\theta_{//}$	8	10	12	deg	Po=100mW
	$\theta_{\perp}$	16	20	22	deg	Po=100mW



Specifications are subject to change without notice.

